



# CP1250N3B

## 主要参数 MAIN CHARACTERISTICS

$I_{T(RMS)}$	12A
$V_{DRM}$	800V
$I_{GT(I,II,III)}$	<50mA

## 用途

- 交流开关
- 相位控制

## APPLICATIONS

- AC switching
- Phase control

## 产品特性

- 平面工艺芯片，高可靠性和一致性
- 三象限可控硅，触发电流的一致性好
- 环保 RoHS 产品
- 150℃ 高结温产品

## FEATURES

- The planar process chip for reliability and uniform
- Uniform gate trigger currents in three quadrants
- RoHS products
- 150℃ High operating junction temperature

## 订货信息 ORDER MESSAGES

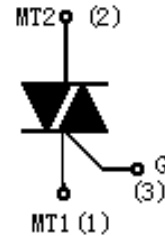
订货型号 Order codes				印 记 Marking	封 装 Package
有卤-条管	无卤-条管	有卤-编带	无卤-编带		
Halogen-Tube	Halogen-Free-Tube	Halogen-Reel	Halogen-Free-Reel		
CP1250N3B -F1-B	CP1250N3B -F1-BR	N/A	N/A	CP1250N3B	TO-220MF-K1

## 概述 GENERAL DESCRIPTION

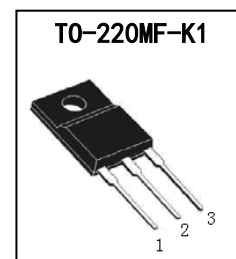
CP1250N3B是平面可控硅芯片结构的三象限双向晶闸管，产品在第四象限不可触发，具有较高的使用可靠性。可适用于容易出现较高dV/dt或dI/dt的交流全波控制线路中，特别推荐应用与电感性负载控制（如电机控制线路）。器件封装形式有TO-220MF-K1 (plastic envelope)。

CP1250N3B are The planar process chip three quadrant triacs, designed for high performance full-wave ac control applications where high static and dynamic dV/dt and high dI/dt can occur. They are specially recommended for use on inductive loads such as motor control circuits. Available packages are TO-220MF-K1 (plastic envelope).

## 封装 Package



序号 Pin	引线名称 Description
1	主电极 1 MT1
2	主电极 2 MT2
3	门极 G



绝对最大额定值 ABSOLUTE RATINGS ( $T_c=25^\circ\text{C}$ )

项 目 Parameter	符 号 Symbol	试 验 条 件 Condition	数 值 Value	单 位 Unit
重复峰值断态电压 Repetitive peak off-state voltage	$V_{\text{DRM}}$		$\pm 800$	V
通态方均根电流 On-state RMS current	$I_{\text{T(RMS)}}$	full sine wave,	12	A
非重复浪涌峰值通态电流 Non-repetitive surge peak on-state current	$I_{\text{TSM}}$	full sine wave , $t=20\text{ms}$	140	A
		full sine wave , $t=16.7\text{ms}$	150	A
		$I^2t$	$t=10\text{ms}$	98
通态电流临界上升率 Repetitive rate of rise of on-state current after triggering	$di/dt$	$I_{\text{TM}}=20\text{A}$ , $I_{\text{G}}=0.2\text{A}$ , $di_{\text{G}}/dt=0.2\text{A}/\mu\text{s}$	100	$\text{A}/\mu\text{s}$
峰值门极电流 Peak gate current	$I_{\text{GM}}$		2	A
峰值门极电压 Peak gate voltage	$V_{\text{GM}}$		5	V
峰值门极功率 Peak gate power	$P_{\text{GM}}$		5	W
平均门极功率 Average gate power	$P_{\text{G(AV)}}$	over any 20ms period	0.5	W
存储温度 Storage temperature	$T_{\text{stg}}$		-40~150	$^\circ\text{C}$
操作结温 Operation junction temperature	$T_{\text{VJ}}$		-40~150	$^\circ\text{C}$



电特性 ELECTRICAL CHARACTERISTIC (T<sub>c</sub>=25°C)

项 目 Parameter	符 号 Symbol	测 试 条 件 Condition	最小 Min	典型 Typ	最大 Max	单位 Unit
峰值重复断态电流 Peak Repetitive Blocking Current	I <sub>DRM</sub>	V <sub>DM</sub> =V <sub>DRM</sub> , T <sub>j</sub> =150°C, gate open		--	2.0	mA
峰值通态电压 Peak on-state voltage	V <sub>TM</sub>	I <sub>TM</sub> =18A, T <sub>j</sub> =25°C,		--	1.5	V
门极触发电流 Gate trigger current	I <sub>GT</sub>	V <sub>DM</sub> =12V, R <sub>L</sub> =100 Ω	MT1(-),MT2(+),G(+)	--	50	mA
			MT1(-),MT2(+),G(-)	--	50	mA
			MT1(+),MT2(-),G(-)	--	50	mA
门极触发电压 Gate trigger voltage	V <sub>GT</sub>	V <sub>DM</sub> =12V, R <sub>L</sub> =100 Ω	MT1(-),MT2(+),G(+)	0.7	1.5	V
			MT1(-),MT2(+),G(-)	0.7	1.5	V
			MT1(+),MT2(-),G(-)	0.7	1.5	V
维持电流 Holding current	I <sub>H</sub>	V <sub>DM</sub> =12V, I <sub>GT</sub> =0.1A		--	60	mA
擎住电流 Latching current	I <sub>L</sub>	V <sub>DM</sub> =12V, I <sub>GT</sub> =0.1A	MT1(-),MT2(+),G(+)	-	60	mA
			MT1(-),MT2(+),G(-)	-	90	mA
			MT1(+),MT2(-),G(-)	-	60	mA
断态临界电压上升率 Rise of off- state voltage	dV/dt	V <sub>DM</sub> =67% V <sub>DRM(MAX)</sub> , T <sub>j</sub> =150°C, gate open	1000	-	-	V/μs
门极开通时间 Gate controlled turn-on time	t <sub>gt</sub>	I <sub>TM</sub> =20A, V <sub>DM</sub> =V <sub>DRM(MAX)</sub> , I <sub>G</sub> =0.1A, dI <sub>G</sub> /dt=5A/μs	-	2	-	μs

## 热特性 THERMAL CHARACTERISTIC

项 目 Parameter	符 号 Symbol	条 件 Condition	最小 Min	典型 Typ	最大 Max	单位 Unit
结到管壳的热阻 Thermal resistance junction to case	R <sub>th(j-c)</sub>	full cycle(TO-220MF-K1)			4.0	°C/W

## 电绝缘特性 ELECTRICAL ISOLATION

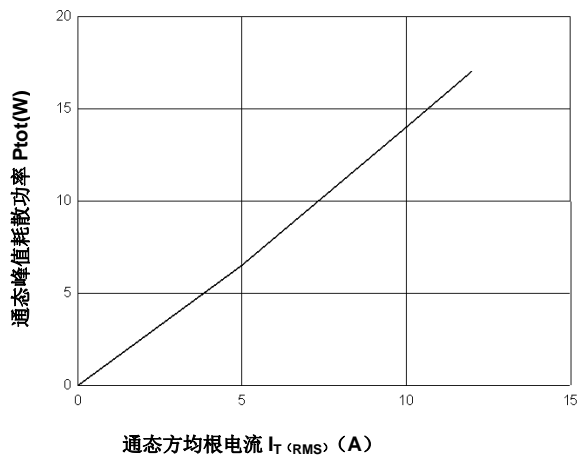
项 目 Parameter	符 号 Symbol	条 件 Condition	数 值 Value	单 位 Unit
绝缘电压 Isolation voltage	V <sub>ISOL</sub>	1 minute, leads to mounting tab TO-220MF-K1	2000	V



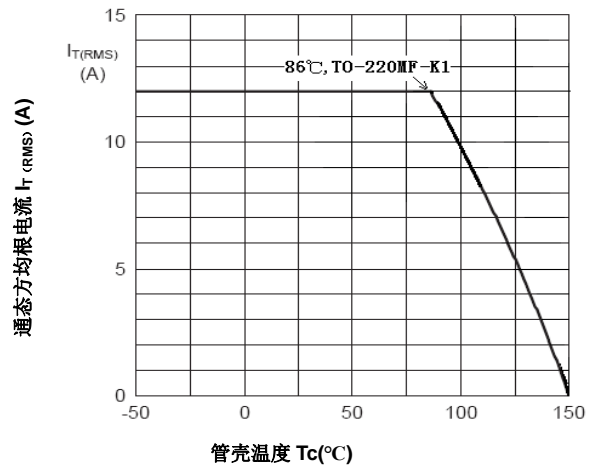


特征曲线 ELECTRICAL CHARACTERISTICS (curves)

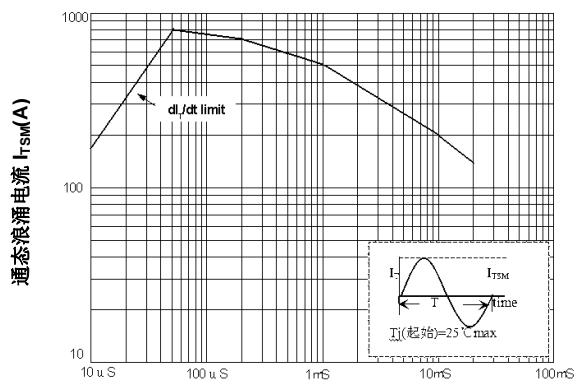
$P_{tot} - I_{T(RMS)}$



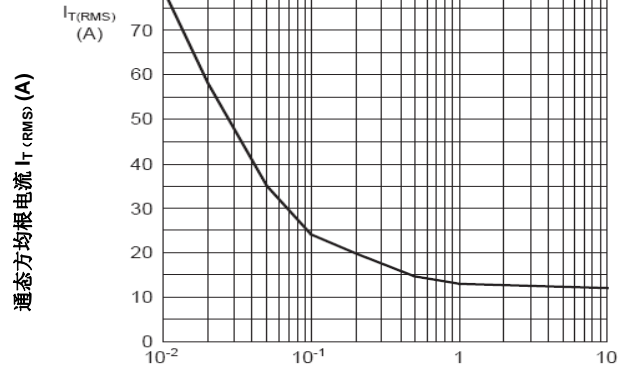
$I_{T(RMS)} - T_c$



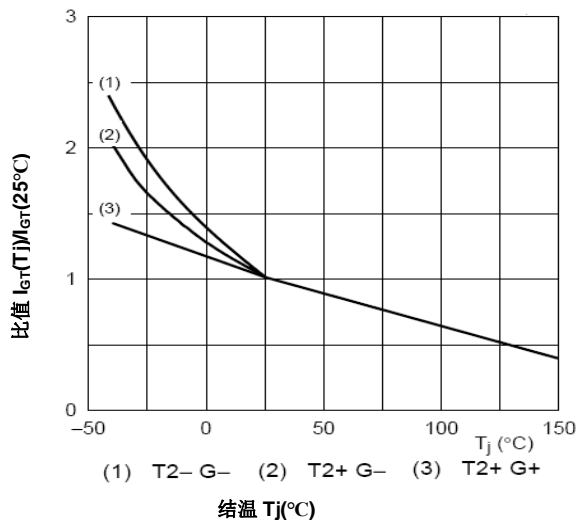
$I_{TSM} - tp$



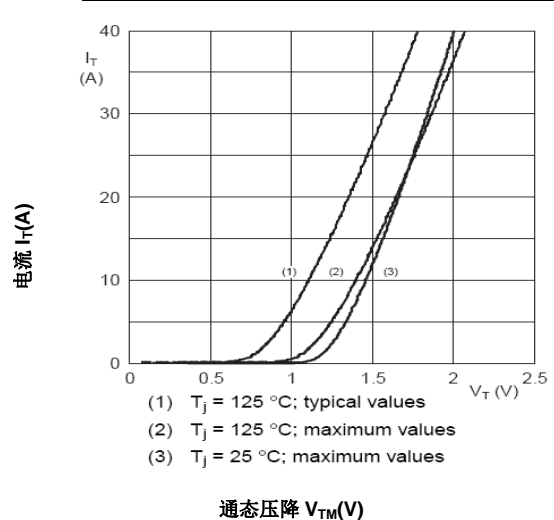
$I_{T(RMS)} - ts$



$I_{GT}(T_j)/I_{GT}(25°C) - T_j$



$V_{TM} - I_T$

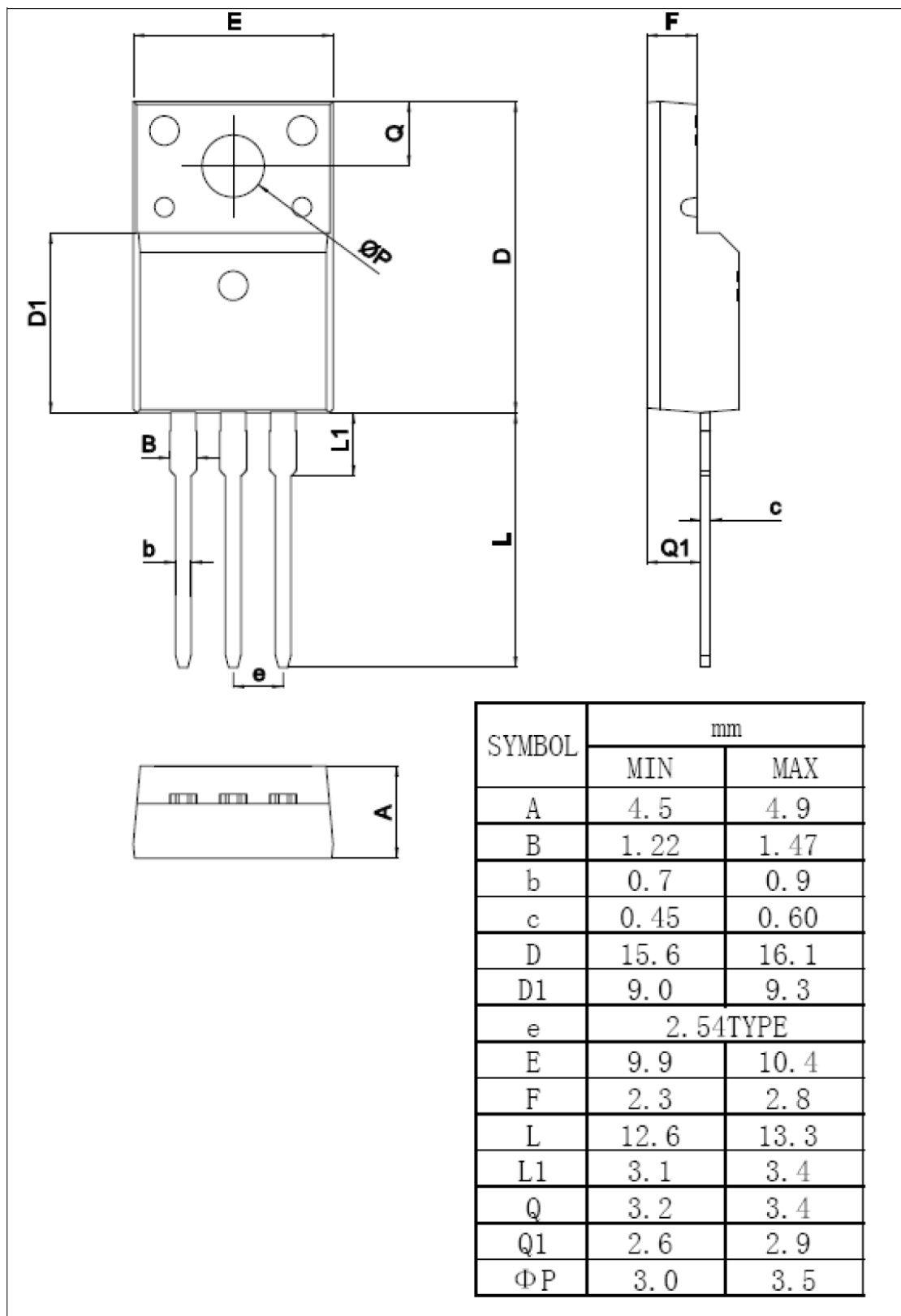




## 外形尺寸 PACKAGE MECHANICAL DATA

TO-220MF-K1

单位 Unit : mm





**注意事项**

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4. 本说明书如有版本变更不另外告知

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3. Please do not exceed the absolute maximum ratings of the device when circuit designing.
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